



PSMN165-200K,518 Information



For Reference Only

Part Number PSMN165-200K,518 Manufacturer Nexperia USA Inc.

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 200V 2.9A SOT96-1**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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PSMN165-200K,518 Specifications

Manufacturer Part Number PSMN165-200K,518 Manufacturer Nexperia USA Inc. Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-SOIC (0.154", 3.90mm Width) Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) #20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature June Mounting Type Surface Mount Supplier Device Package Package / Case Package / Case SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	PSMN165-200K,518
Package 8-SOIC (0.154", 3.90mm Width) Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ ImA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	Nexperia USA Inc.
Package 8-SOIC (0.154", 3.90mm Width) Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series TrenchMOS? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 200V Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature Surplier Device Package Package / Case MOSFET (Metal Oxide) 200V 200V 2.9A (Tc) 10V 4V @ 1mA 4V @ 1mA 40nC @ 10V 1330pF @ 25V 220V FET Feature - C Surface Mount Surface Mount Surface Mount Supplier Device Package 8-SO 8-SOIC (0.154", 3.90mm Width)	Series	TrenchMOS?
Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 2.9A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature Supplier Device Package Package / Case 2.9A (Tc) 2.9A (Tc) 2.9A (Tc) 2.9A (Tc) 3.5V The continuous Drain (Id) @ 25°C 2.9A (Tc) 2.9A (Tc) 3.5V The continuous Drain (Id) @ 25°C 2.9A (Tc) 3.5V The continuous Drain (Id) @ 25°C 2.9A (Tc) 3.5V The continuous Drain (Id) @ 25°C 2.9A (Tc) 3.5V The continuous Drain (Id) @ 25°C 40°C The continuous Properties (Id) & The continuo	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 10V 40nC @ 10V 1330pF @ 25V ±20V FET Feature - - Surface Mount Surface Mount Supplier Device Package 8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	200V
Vgs(th) (Max) @ Id 4V @ 1mA Gate Charge (Qg) (Max) @ Vgs 40nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	2.9A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1330pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	4V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)3.5W (Tc)Rds On (Max) @ Id, Vgs165 mOhm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	40nC @ 10V
FET Feature - Power Dissipation (Max) 3.5W (Tc) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1330pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 165 mOhm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs165 mOhm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	3.5W (Tc)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	165 mOhm @ 2.5A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

PSMN165-200K,518 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

PSMN165-200K,518 Payment Methods



















PSMN165-200K,518 Shipping Methods













If you have any question about PSMN165-200K,518, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com